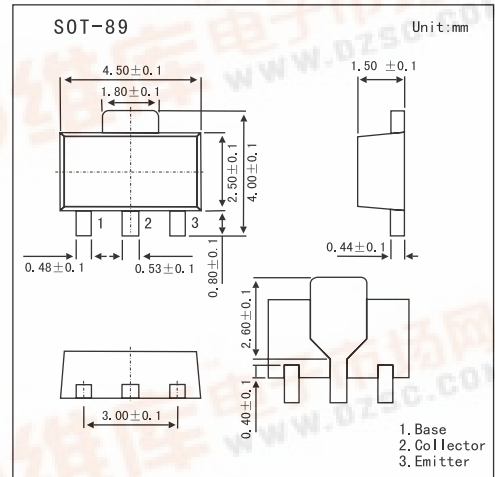


SMD Type Transistors

Silicon NPN Epitaxial
2SD1367

■ Features

- Low frequency power amplifier.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector to base voltage	V _{CB0}	20	V
Collector to emitter voltage	V _{CEO}	16	V
Emitter to base voltage	V _{EBO}	6	V
Collector current	I _C	2	A
Peak collector current	I _{CP} *1	3	A
Collector power dissipation	P _C *2	1	W
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

*1. PW ≤ 10 ms; d ≤ 0.02.

*2. Value on the alumina ceramic board (12.5 X 20 X 0.7 mm)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector to base breakdown voltage	V _{(BR)CBO}	I _C = 10 μA, I _E = 0	20			V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _C = 1 mA, R _{BE} = ∞	16			V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = 10 μA, I _C = 0	6			V
Collector cutoff current	I _{CBO}	V _{CB} = 16 V, I _E = 0			0.1	μA
Emitter cutoff current	I _{EBO}	V _{EB} = 5 V, I _C = 0			0.1	μA
DC current transfer ratio	h _{FE}	V _{CE} = 2 V, I _C = 0.1 A	100		500	
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = 1 A, I _B = 0.1 A		0.15	0.3	V
Base to emitter saturation voltage	V _{BE(sat)}	I _C = 1 A, I _B = 0.1 A		0.9	1.2	V
Gain bandwidth product	f _T	V _{CE} = 2 V, I _C = 10 mA		100		MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz		20		pF

■ hFE Classification

Marking	BA	BB	BC
hFE	100~200	160~320	250~500

